



N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

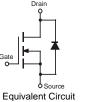
Features

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating
- Lead, Halogen and Antimony Free, RoHS Compliant
 "Green" Device (Notes 2 and 4)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)







TOP VIEW

TOP VIEW

Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Charact	eristic	Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	100	V	
Drain-Gate Voltage $R_{GS} \le 20 K\Omega$		V _{DGR}	100	V	
Gate-Source Voltage	Continuous	V _{GSS}	±20	V	
Drain Current (Note 1)	Continuous Pulsed	I _D I _{DM}	170 680	mA	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 1)	Pd	300	mW	
Thermal Resistance, Junction to Ambient (Note 1)	R _{0JA}	417	°C/W	
Operating and Storage Temperature Range	Tj, T _{STG}	-55 to +150	°C	

Electrical Characteristics @T_A = 25°C unless otherwise specified

						r		
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 3)								
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$		
Zero Gate Voltage Drain Current	I _{DSS}	_		1.0	μA	$V_{DS} = 100V, V_{GS} = 0V$		
				10	nA	$V_{DS} = 20V, V_{GS} = 0V$		
Gate-Body Leakage, Forward	I _{GSSF}		_	50	nA	$V_{GS} = 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 3)								
Gate Threshold Voltage	V _{GS(th)}	0.8	1.4	2.0	V	$V_{DS} = V_{GS}, I_D = 1mA$		
Static Drain-Source On-Resistance			_	6.0	Ω	$V_{GS} = 10V, I_D = 0.17A$		
	R _{DS (ON)}			10		V _{GS} = 4.5V, I _D = 0.17A		
Forward Transconductance	g fs	80	370		mS	V _{DS} = 10V, I _D = 0.17A, f = 1.0KHz		
Drain-Source Diode Forward Voltage	V _{SD}		0.84	1.3	V	$V_{GS} = 0V, I_{S} = 0.34A$		
DYNAMIC CHARACTERISTICS								
Input Capacitance	Ciss	_	29	60	pF			
Output Capacitance	Coss	_	10	15	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$		
Reverse Transfer Capacitance	Crss	_	2	6	pF			
SWITCHING CHARACTERISTICS								
Turn-On Rise Time	tr	_	_	8	ns			
Turn-Off Fall Time	t _f			16	ns	$V_{DD} = 30V, I_D = 0.28A,$		
Turn-On Delay Time	t _{D(ON)}	_		8	ns	R _{GEN} = 50Ω, V _{GS} = 10V		
Turn-Off Delay Time	t _{D(OFF)}			13	ns]		

Notes: 1. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. 2. No purposefully added lead. Halogen and Antimony Free.

Short duration pulse test used to minimize self-heating effect.

Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.



NEW PRODUCT

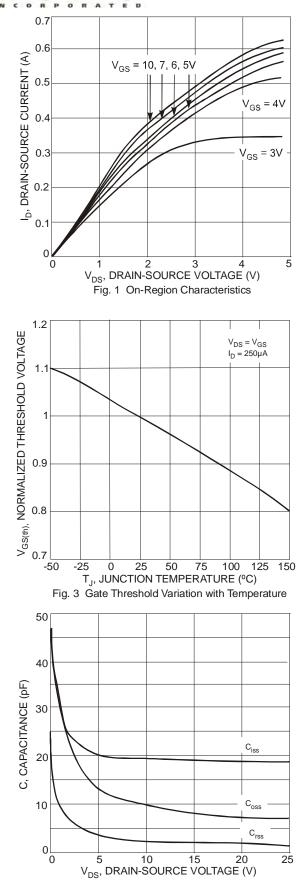
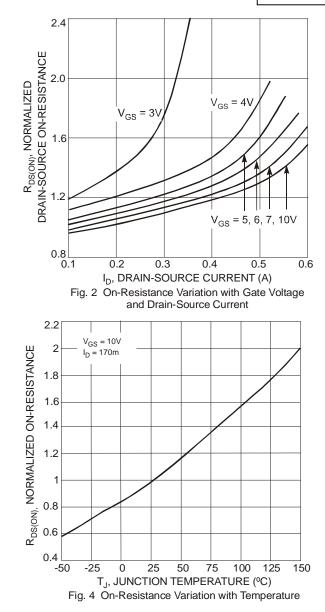


Fig. 5 Typical Capacitance



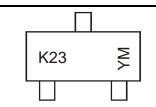


Ordering Information (Note 5)

Part Number	Case	Packaging
BSS123-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

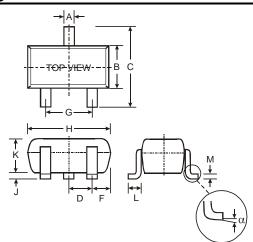


 $\begin{array}{l} \mathsf{K23} = \mathsf{Product} \ \mathsf{Type} \ \mathsf{Marking} \ \mathsf{Code} \\ \mathsf{YM} = \mathsf{Date} \ \mathsf{Code} \ \mathsf{Marking} \\ \mathsf{Y} = \mathsf{Year} \ \mathsf{ex:} \ \mathsf{T} = 2006 \\ \mathsf{M} = \mathsf{Month} \ \mathsf{ex:} \ \mathsf{9} = \mathsf{September} \end{array}$

Date Code Key

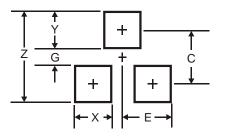
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Year	200	6	2007		2008	20	09	2010		2011	2	012
Code	Т		U		V	V	N	Х		Y		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

Package Outline Dimensions



SOT-23						
Dim	Dim Min Max					
Α	0.37	0.51				
В	1.20	1.40				
C	2.30	2.50				
D	0.89	1.03				
F	0.45	0.60				
G	1.78	2.05				
Н	2.80	3.00				
J	0.013	0.10				
K	K 0.903 1.10					
L	L 0.45 0.61					
М	0.085	0.180				
α	0°	8°				
All Dir	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Y	1.4
С	2.0
E	0.9

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